

forming a silicon oxide film on said semiconductor film;
disposing a solution in contact with said silicon oxide film, said solution containing a metal being capable of promoting crystallization of said semiconductor film;
heating said semiconductor film and said metal to crystallize said semiconductor film;
and
irradiating laser beam to said semiconductor film to improve the crystallinity thereof.

²
~~61~~. (Amended) A method according to claim ¹~~60~~ wherein said CVD system is selected from a plasma CVD system and an LPCVD system.

⁶
~~73~~. (Amended) A method according to claim ⁵~~72~~ wherein said CVD system is selected from a plasma CVD system and an LPCVD system.

⁹
~~84~~. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;
forming a semiconductor film comprising amorphous silicon on said silicon nitride film;
forming a silicon oxide film on said semiconductor film;
disposing a solution in contact with said silicon oxide film, said solution containing a metal being capable of promoting crystallization of said semiconductor film; and
heating said semiconductor film and said metal to crystallize said semiconductor film.

Please add new claims 85-91 as follows:

¹⁰
~~85.~~ (New) A method according to claim ⁹~~84~~ wherein said metal is selected from the group consisting of nickel, palladium, platinum, copper, silver, gold, indium, tin, phosphorous, arsenic and antimony.

¹¹
~~86.~~ (New) A method of manufacturing a semiconductor device comprising the steps of:
forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;
forming a semiconductor film comprising amorphous silicon on said silicon nitride film;
forming a silicon oxide film on said semiconductor film;
disposing a solution comprising a metal compound in contact with said silicon oxide film; and
heating said semiconductor film to crystallize said semiconductor film.

¹²
~~87.~~ (New) A method according to claim ¹¹~~86~~ wherein said metal compound is selected from the group consisting of nickel bromide, nickel acetate, nickel oxalate, nickel carbonate, nickel chloride, nickel iodide, nickel nitrate, nickel sulfate, nickel formate, nickel acetylacetonate, nickel 4-cyclohexybutyrate, and nickel hydroxide.

¹³
~~88.~~ (New) A method of manufacturing a semiconductor device comprising the steps of:
forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;
forming a semiconductor film comprising amorphous silicon on said silicon nitride film;
forming a silicon oxide film on said semiconductor film;
disposing a solution in contact with said silicon oxide film, said solution containing a metal being capable of promoting crystallization of said semiconductor film;

heating said semiconductor film and said metal to crystallize said semiconductor film;
and
irradiating laser beam to said semiconductor film to improve the crystallinity thereof.

¹⁴
~~89~~. (New) A method according to claim ¹³~~88~~ wherein said metal is selected from the group consisting of nickel, palladium, platinum, copper, silver, gold, indium, tin, phosphorous, arsenic and antimony.

¹⁵
~~90~~. (New) A method of manufacturing a semiconductor device comprising the steps of:
forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;
forming a semiconductor film comprising amorphous silicon on said silicon nitride film;
forming a silicon oxide film on said semiconductor film;
disposing a solution comprising a metal compound in contact with said silicon oxide film;
heating said semiconductor film to crystallize said semiconductor film; and
irradiating laser beam to said semiconductor film to improve the crystallinity thereof.

¹⁶
~~91~~. (New) A method according to claim ¹⁵~~90~~ wherein said metal compound is selected from the group consisting of nickel bromide, nickel acetate, nickel oxalate, nickel carbonate, nickel chloride, nickel iodide, nickel nitrate, nickel sulfate, nickel formate, nickel acetylacetonate, nickel 4-cyclohexybutyrate, and nickel hydroxide. --

L1 conc.